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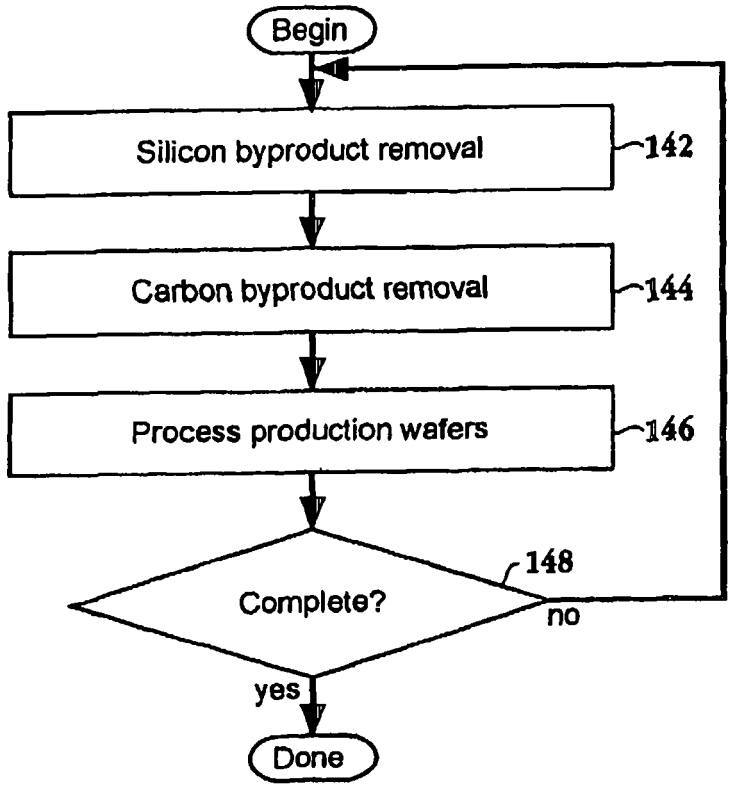
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(54) Title: HIGH PRESSURE WAFER-LESS AUTO CLEAN FOR ETCH APPLICATIONS



(57) Abstract: A method for cleaning a processing chamber is provided. The method initiates with introducing a fluorine containing gaseous mixture into a processing chamber. Then, a plasma is created from the fluorine containing gaseous mixture in the processing chamber. Next, a chamber pressure is established that corresponds to a threshold ion energy in which ions of the plasma clean inner surfaces of the processing chamber without leaving a residue. A method for substantially eliminating residual aluminum fluoride particles deposited by an in-situ cleaning process for a semiconductor processing chamber and a plasma processing system for executing an in-situ cleaning process are also provided.

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